

ABSTRACT

The solution is useful for removing a barrier material from a semiconductor substrate. The solution comprises, by weight percent, 0.01 to 25 oxidizer, 0 to 15 inhibitor for a nonferrous metal, 0 to 15 abrasive, 0 to 20 complexing agent for the nonferrous metal, 0.01 to 12 barrier removal agent and balance water. The barrier removal agent is selected from the group comprising imine derivative compounds, hydrazine derivative compounds and mixtures thereof.